## E lectronic Structure and E lectron-P honon C oupling in the 18K Superconductor Y $_2$ C $_3$

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The electronic structure and electron-phonon coupling in  $Y_2C_3$  is investigated using density functional calculations. We nd that the Ferm i level falls in a manifold of mixed character derived from Y d states and antibonding states associated with the C dimers in the structure. Calculations of the electron-phonon coupling for Y and C modes show that the former provide most of the coupling. M odes associated with C-C bond stretching have large matrix elements, but make sm all contributions to the coupling because of their high phonon frequencies. Substantial electron doping of the C-C antibonding states would yield a large increase in the coupling and critical temperature, perhaps to values comparable to M gB<sub>2</sub>. However, it seems unlikely that a modi cation of  $Y_2C_3$  with much higher lling of the C-C antibonding states can be stabilized.

The rare earth sesquicarbides,  $R_2C_3$ , where R is a rare earth or Y are a fam ily of superconducting m aterials that form in the bcc Pu<sub>2</sub>C<sub>3</sub> structure under high temperature conditions. Sam ples produced by arc melting have critical tem peratures, T<sub>c</sub>, of 10K to 12K, with little dependence on the particular rare earth. For example, as synthesized samples with the largest and sm allest rare earths, speci cally, LaC3 and Y2C3 have critical tem peratures of 11K and 10.5K, respectively.<sup>1{5</sup> However, it was found early on that heavy Th doping raises T<sub>c</sub>, up to 17K in the case of the Y compound.<sup>6</sup> Very recently, Am ano and co-workers<sup>7</sup> reported that  $T_c$  for  $Y_2C_3$  could be increased to 18K by synthesis under high pressure (4-5.5 GPa). The resulting samples have the same  $Pu_2C_3$ structure as previously obtained sam ples but a slightly di erent lattice param eter, suggesting that the e ect of pressure is to change the composition of the samples. Furtherm ore, they reported that the results were sensitive to the sintering conditions. The lattice parameters varied in the range a=  $8.181A \{ 8.226A, w \text{ ith reported } T_{c} \}$ spanning the range 15K to 18K. The extrapolated upper critical eld of the 18K samples was estimated to be 30T .8

The Pu<sub>2</sub>C<sub>3</sub> structure has four form ula units per prim itive unit cell, spacegroup I43d, Y on site 16c (u,u,u) and C on site 24d  $(v_0, 1/4)$ , where the coordinates are in term s of the bcc lattice vectors (see Fig. 1). A s m ay be seen, C dim ers with short bond lengths are a characteristic of this structure. E lectronic structure studies of other m etals with C dim ers both at the tight binding<sup>9</sup> and density functional level<sup>10</sup> suggest that the electronic structure could have substantial C-C antibonding character near the Ferm i level. Such states m ay be expected to have extrem ely high deform ation potentials, re ecting these very strong C-C triple bonds. Also re ecting the very strong covalent bonds, phonons that m odulate the C-C distances would be very sti, which, if these states were responsible for the superconductivity, would yield a m oderate electron-phonon coupling, , and a very high logarithm ic average phonon frequency and therefore high

prefactor in the M dM illan equation for  $T_{\rm c}$ . In this scenario, a very strong dependence of  $T_{\rm c}$  on stoichiom etry (m ore precisely, occupation of the antibonding states) m ight be anticipated, as well as the possibility of very high  $T_{\rm c}$  in m ore optim ally doped sam ples, perhaps with values like in M gB $_2$  and A  $_3C_{60}$ . Here we report density functional calculations of the electronic structure and the coupling constants of a C-C and an Y m ode aim ed at determ ining the extent to which this scenario applies in Y $_2C_3$ .

The present calculations were done using the general potential linearized augm ented planew ave (LAPW )  $m = thod_{r}^{12}$  with local orbital extensions<sup>13</sup> to relax linearization errors and to treat the sem i-core states of Y . LAPW sphere radii of 2.0  $a_0$  and 1.24  $a_0$  were used for Y and C, respectively. W ell converged basis sets (convergence tests were done) consisting of 4250 basis functions for the 20 atom prim it ive cell were used, along with converged Brillouin zone samplings. The core states were treated relativistically and valence states sem irelativistically. For the crystal structure we used the reported bcc I43d Pu<sub>2</sub>C<sub>3</sub> structure with the experimentally determ ined lattice parameter, a = 8226 A, from Ref. 7 but relaxed the internal coordinates using the calculated atom ic forces. W e found signi cant changes in the C-C dim erbond length from the available experim ental re nement (Ref. 11). Speci cally, we obtain a C-C distance of 1.33~A , and a Y-C distance of 2.51 A , corresponding to internal parameters, u = 0.0504 and v = 0.2940. The corresponding full sym m etry R am an m odes are an Y dom inated mode at 175 cm  $^{\rm 1}\,$  and an alm ost pure C-C bond stretching mode at 1442 cm  $^{1}$  . It seems likely that the di erence between our results and the C position of Ref. 11 is related to di culty in the re nem ent due to sam ple stoichiom etry, which is an issue in these sesquicarbides, as m entioned above.

The calculated electronic band structure and corresponding electronic density of states  $(D \cap S)$  are given in Figs. 2 and 3, respectively. The Ferm i surfaces are displayed in Fig. 5. The band structure agrees qualitatively with a very recent report by Shein and Ivanovskii,  $^{14}$  although there are noticable di erences in detail, presum - ably related to the di erent C-C bond length in that calculation.

The band structure shows a manifold of 12 C 2s derived bands extending from -14.9 eV to -6.2 eV, relative to the Ferm ienergy,  $E_F$  (note that there are 12 C atom s in the primitive cell). This is followed by a narrower manifold of 18 C 2p bonding bands, associated with the C dimers. This, in turn, is separated by a 2.5 eV gap from a broad manifold of mixed C-C antibonding and Y character. The Ferm ilevellies 1 eV from the bottom of this manifold. Fig. 4 shows the contribution from states near  $E_F$  to the charge density. The plot is for the energy range that contributes 1 e per unit cell going down from  $E_F$ . This electronic structure is consistent with a conventional picture<sup>9</sup> of strongly covalently bonded C dimers embedded in a solid that has metallic cohesion involving mixture of Y and antibonding C-C states.

As may be seen, there are several bands crossing the  $E_F$ . This leads to a complex multisheet Ferm i surface (Fig. 5), with no obvious strong nesting features.<sup>15</sup> The density of states at E  $_{\rm F}~$  is N (E  $_{\rm F}$  ) = 1.88 eV  $^1~$  on a per formula unit both spins basis, corresponding to a bare linear speci c heat coe cient,  $bare = 4.4 \text{ mJ/molK}^2$ . This is approximately 60% larger than the experimental value of  $= 2.8 \text{ mJ/molK}^2$  (ref. 2), but this comparison should be interpreted with caution since the experim ental stoichiom etry was not well established. W e note that Th doped  $Y_2C_3$  with  $T_c = 17K$  (closer to the 18K reported for Y<sub>2</sub>C<sub>3</sub> by Am ano and co-workers), has a reported experimental =  $4.7 \text{ mJ/molK}^2$ , and that the DOS is peaked at the stoichiom etric com position, im plying that o -stoichiom etric sam ples would likely have lower, both because of lower  $_{\rm bare}$  and presumably lower electron phonon enhancem ent.

Considering the apparent absence of strong nesting, and the large unit cell (four formula units, 20 atom s), it is expected that the zone center modes may be at least sem i-quantitatively representative for determ ining the electron-phonon coupling. As a further simpli cation, we focus on two modes in order to obtain the gross features. These are the two full sym metry modes related to the internal structural parameters. As mentioned, these are an Y dominated mode at 175 cm  $^{\rm 1}$  and an alm ost pure C-C bond stretching mode at 1442 cm  $^{1}$  . We determ ined the mode for these two modes using a frozen phonon method, in which LDA calculations were done as a function of the phonon distortion, and the deform ation potentials calculated directly from the change in electronic structure on the Ferm i surface. The result is shown as a function of rigid band Ferm i energy in Fig. 6. For this plot, it was assumed that the lower frequency Y mode (which modulates both Y distances and Y-C distances) is representative of all modes except the 6 C-C bond stretching m odes, which were assumed to be represented by the high frequency C -C m ode. M ost likely, this is reasonably good for the bond stretching m odes but underestim ates the phonon frequency for the other modes, since the C dimers are lighter than an Y atom. However, considering the crudeness of representing the system with two full symmetry zone center modes, it hardly seems justi ed to attempt corrections, and instead we view the result as sem i-quantitative.

The calculated electron-phonon coupling for the stoichiom etric band lling is = 0.6 and is dom inated by phonons other than the C-C bond stretching; the C-C bond stretching provides less than 10% of the total . Inserting = 0.6 into the M cM illan formula, with = 0.1 and != 175 cm<sup>-1</sup>, we obtain  $T_c$ = 5K, which is fair agreement considering the crudeness of the approximation em – ployed.

W hat is signi cant is that has a maximum at the stoichiom etric band lling. This is related to the fact that the Ferm ienergy falls on a peak in the DOS. The dependence of on band lling and the di cult synthesis of stoichiom etric sesquicarbides provides an explanation for the experim entally observed variability of  $T_c$  depending on preparation conditions. Going to low er band lling, decreases and then increases again to a value exceeding

= 1, re ecting the structure of the DOS, but this only happens quite far down, corresponding to an electron de-

ciency of about 1 e per form u la unit. The C-C streething contribution is sm all throughout this region. Going to higher electron count, again decreases initially and then increases, again to values exceeding = 1. However, in this case the C-C bond stretching contribution becomes signi cant and as a result the logarithm ic average phonon frequency also sharply increases. In principle, this would mean that heavily electron doped  $Y_2C_3$  would become a high temperature superconductor, like M gB<sub>2</sub> and A<sub>3</sub>C<sub>60</sub>. How ever, this is based on a rigid band lling, which is a highly unlikely scenario. Instead, population of C-C antibonding states should be highly disfavored, and therefore it would be rather di cult to chem ically reach the region where this contribution to become s large.

In sum m ary, we report electronic structure and m ode electron-phonon calculations for  $Y_2C_3$ . The results are consistent with conventional electron-phonon m ediated superconductivity related to Y - C phonons. The results show that the superconductivity is qualitatively like in other m etal carbide superconductors, and not like M gB<sub>2</sub> or  $A_3C_{60}$ .

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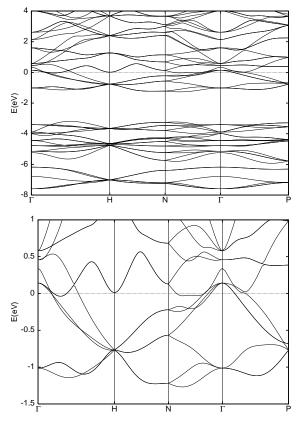


FIG.2. Calculated band structure of  $Y_2C_3$  with the relaxed atom ic positions. The lowest bands shown are part of the C 2s manifold. The bottom of this manifold is at -14.9 eV. The lower panel is a blow-up around  $E_{\rm F}$ , which is at 0 eV.

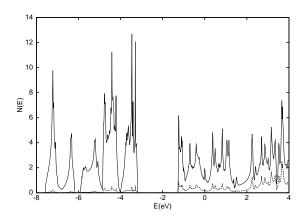


FIG.3. Electronic density of states of  $Y_2C_3$  with the relaxed atom ic positions. The solid line is the total density of states on a per form ula unit basis and the dashed line is the Y d contribution as de ned by projection onto the Y LAPW sphere of radius 2.0  $a_0$ .

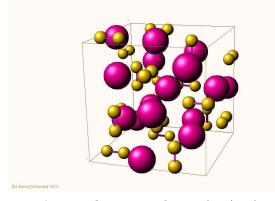


FIG .1. Crystal structure of  $Y_2\,C_3$  showing the  $C_2\,$  dimers. Large spheres denote  $Y\,$  and sm all spheres denote C .

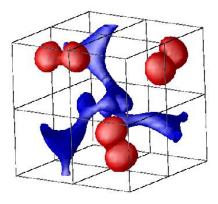
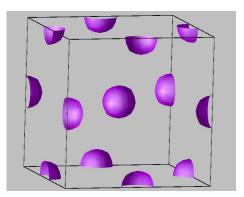


FIG.4. This gure shows the charge density originating from the valence bands near  $E_F$  (see text) in 1/4 of the prim itive unit cell around C (dum bells, red on line) and Y (interconnected network, blue on line). Isodensity surfaces correspond to (r) = 0.00112 e/a<sub>0</sub><sup>3</sup> for C and 0.00092 e/a<sub>0</sub><sup>3</sup> for Y. Sm all di erences between the charge density values were needed to im prove visibility of the two surfaces. For the same puprose, the parts of the Y charge density surfaces, penetrating from the neighboring unit cells, were rem oved. Note the m etallic like Y derived density and the C antibonding density.



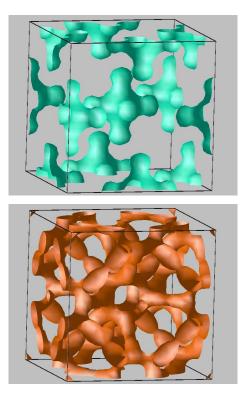


FIG.5. LDA Ferm isurfaces of Y  $_2$ C  $_3$ .

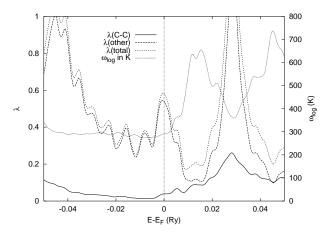


FIG.6. Mode and average phonon frequency (see text) as a function of energy. The heavy dashed (heavy solid) line denotes the full symmetry Y (C) derived mode as a function of energy, normalized as if these modes are representative. The light dashed line is the total with this assumption. The light dotted line is the logarithm ic average of these two frequencies with , which would enter the prefactor of the M cM illan equation.